



**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

Applicant: Doak et al. : Group Art Unit: 2822  
Serial No.: 09/887,777 : Examiner: Parviz Hassanzadeh  
Filed: June 22, 2001 :  
Title: **Method and Apparatus for Preparing Nitride Semiconductor Surfaces**

**RESPONSE TO OFFICIAL ACTION**

Box Non-Fee Amendment  
Commissioner for Patents  
Washington, D.C. 20231

Dear Sir:

In response to the Official Action mailed September 25, 2002, please amend and reconsider the above-identified application as shown below and in view of the remarks that follow.

**In the Specification**

Substitute enclosed new pages 6 and 7 for those presently in the application.

**In the Claims**

Cancel nonelected claims 2 - 11 and 19 - 35, without prejudice.

Kindly substitute the following rewritten claims 12 - 15 and 36 for those currently appearing in the application and kindly add the following new claims 39 - 52.

12. (Amended) An apparatus for producing nitride films comprising:
- (a) a pair of corona-discharge producing electrodes,
  - (b) a nitrogen delivery path leading to a nozzle at which the electrodes produce a corona discharge, and
  - (c) means to locate a substrate along the nitrogen delivery path downstream of the location at which the electrodes produce the corona discharge for deposition thereon of nitrogen activated by the corona discharge at a location sufficiently distant from the corona-

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